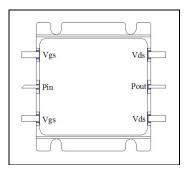
0.8-2.2GHz, 100W, GaN Fully matched PA Module

Description

The GMAH0822-100H3 is a 100-watt, single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from 0.8 to 2.2GHz. The module is 50 Ω input/output matched and requires minimal external components.

The module implements multiple GaN active dice and its matching network within highly compact 30.8*27.4mm metal RF package with excellent capability for heat dissipation.

Vds=32V Idq=250mA Vgs=-2.75V CW						
F	Pin	Psat	Psat	ld	Gain	Eff
(MHz)	(dBm)	(dBm)	(W)	(A)	(dB)	(%)
800	38.62	50.21	105.0	5.15	11.59	63.7
900	40.018	51.278	134.2	6.74	11.26	62.2
1000	40.429	51.269	133.9	6.975	10.84	60.0
1100	41.565	52.165	164.6	9.33	10.6	55.1
1200	41.299	52.159	164.4	8.15	10.86	63.0
1300	40.92	50.95	124.5	6.56	10.03	59.3
1400	40.527	51.067	127.8	7.05	10.54	56.7
1500	40.594	50.634	115.7	6.34	10.04	57.0
1600	41.522	50.762	119.2	7.29	9.24	51.1
1700	40.79	51.29	134.6	7.79	10.5	54.0
1800	39.56	51.34	136.1	8	11.78	53.2
1900	39.211	50.721	118.1	8.32	11.51	44.3
2000	39.324	50.944	124.3	6.82	11.62	56.9
2100	40.204	51.014	126.3	8.53	10.81	46.3
2200	40.209	50.729	118.3	9.04	10.52	40.9



Product Features

- Operating Frequency Range: 0.8-2.2GHz
- Operating Drain Voltage(Recommended): +32V
- 50 Ω Input/Output (External DC block capacitor needed)
- Psat≥50 dBm (CW)
- Small signal gain:>13dB, Power gain:>10dB
- Minimum efficiency:>40%
- 30.8*27.4 mm metal RF package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Innogration (Suzhou) Co., Ltd. Document Number: GMAH0822-100H3 Advanced Datasheet V1.0

Applications

- Ultra Broadband Amplifiers within L band
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

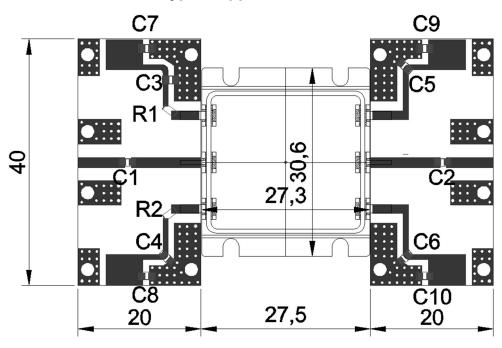
Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
DrainSource Voltage	V _{DSS}	150	Vdc
GateSource Voltage	V _{GS}	-10 to +2	Vdc
Operating Voltage	V _{DD}	+32	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	Tc	+150	°C
Operating Junction Temperature	T₁	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Rejc	4.2	°C/W
T _C = 25°C, Pout=100W, FEA	RejC	1.3	-C/VV

Typical application circuit



Component	Description	Suggested Manufacturer
C7,C8,C9,C10	Ceramic multilayer	10uF/100V
	capacitor, 10uF, 100V	
C1,C3,C4,C5,C6	10pF	MQ200805_Series
C2	15pF	MQ300709_Series
R1	Chip Resistor,10Ω,1206	
PCB	30Mil Rogers 4350B	



TYPICAL CHARACTERISTICS

Figure 1. Network analyzer output S11/S21 (Pin=0dBm)

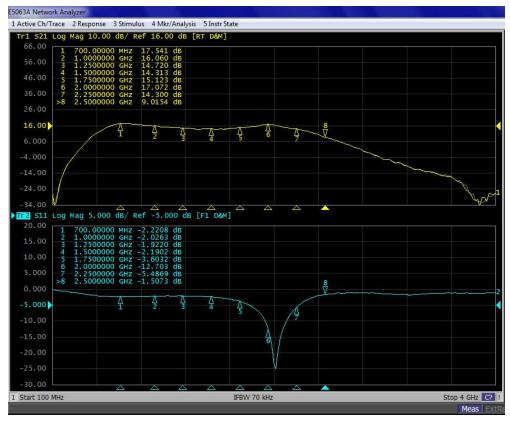
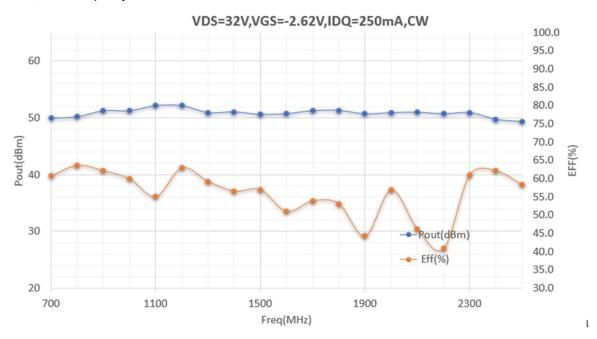
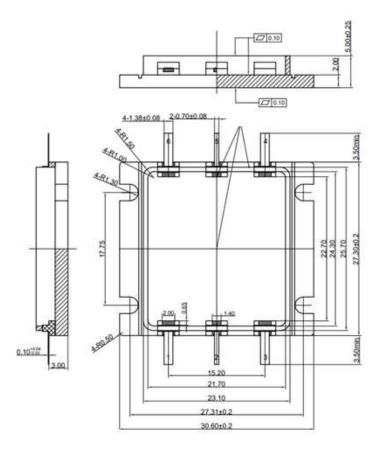


Figure 3. Psat, Eff Vs Frequency across the band



Package Dimensions (Unit:mm)



Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2023/7/17	Rev 1.0	Advanced Datasheet

Application data based on JF-23-05

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